

# MICROWAVE PLASMA SYSTEM MA3000D-521BB

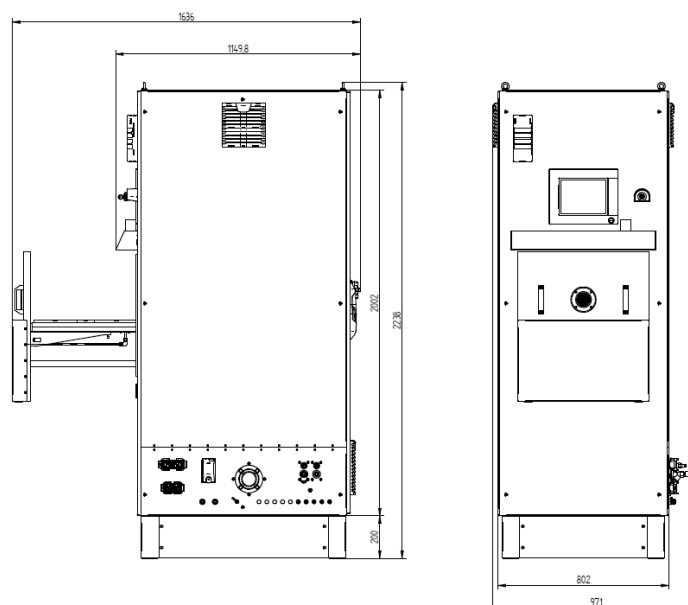
## STRIPPING TOOL



### Features

- Optimized for the removal of thick photoresist layers (e.g. SU-8, KMPR, etc.)
- Unique design for isotropic etching of materials such as Si, SiO<sub>2</sub>, SiN, SiO<sub>x</sub> Ny, W, Mo, etc.
- Pure chemical etching without attack of the substrate by ion bombardment
- Integrated compact RPS (Remote Plasma Source)
- Water cooled plasma zone
- Very low thermal load of the substrate
- Substrate size up to 240 mm x 240 mm
- No attack of metals (Ni, Ni/Fe, Au, Cu, etc.)
- Very high selectivity achievable to Si and Si compounds like SiO<sub>2</sub> or Si<sub>3</sub>N<sub>4</sub>
- High environmental compatibility
- For 5 x 8" or 5 x 6" or 9 x 4" wafers or a substrate size of 500 mm x 500 mm

### Outline Dimensions (mm)



## Specifications

<b>Mains voltage</b>	3~ (L1 / L2 / L3 / PE) 400 V, 50 A, 50 / 60 Hz
<b>Mains leakage current</b>	3,5 mA @ 440/520 VAC/50 Hz
<b>HF output power</b>	3000 W
<b>Cooling</b>	Air / Water ≥ 10 (2,64) l/min (US.gal/min) 4 - 6 (58,02 - 87,02) bar (psi) @ 20 - 25 (68 - 77) °C (°F)
<b>Process gases</b>	O <sub>2</sub> , N <sub>2</sub> , CF <sub>4</sub> , H <sub>2</sub> , SF <sub>6</sub> , -
<b>Vacuum connection</b>	ISO-K63

<b>Dimensions</b>	Width: 957 (37,68) mm (inch) Height: 2200 (86,61) mm (inch) Depth: 1158 (45,59) mm (inch)
<b>Size of working plate</b>	504 x 504 (19,84 x 19,84) mm (inch)
<b>Weight</b>	520 (1146,4) kg (lbs)
<b>Conditions</b>	In operation: 5 °C (41 °F) - 40 °C (104 °F), relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing, 3K3 Storage: - 25 °C (- 13 °F) - + 70 °C (158 °F), 70 kPa - 106 kPa, relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing , 1K3
<b>Frequency</b>	2450 MHz
<b>Compressed air</b>	6 - 9 (87,02 - 130,53) bar (psi) Oil free, dry, 5 µm filtered

## Recommended system components

- Vacuum pump (dry pump min. 300 m<sup>3</sup>/h, recommended 600 m<sup>3</sup>/h)
- Gas cleaning system (CS CLEAN dry absorber)